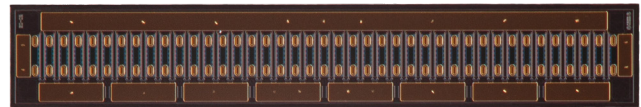


CG2H80120D

120 W, 8.0 GHz, GaN HEMT Die

Description

Cree's CG2H80120D is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity, and higher thermal conductivity. GaN HEMTs offer greater power density and wider bandwidths compared to Si and GaAs transistors



PN: CG2H80120D

Features

- 15 dB Typical Small Signal Gain at 4 GHz
- 12 dB Typical Small Signal Gain at 8 GHz
- 120 W Typical P_{SAT}
- 28 V Operation
- High Breakdown Voltage
- High Temperature Operation
- Up to 8 GHz Operation
- High Efficiency

Applications

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

Packaging Information



- Bare die are shipped in Gel-Pak® containers
- Non-adhesive tacky membrane immobilizes die during shipment

 Large Signal Models Available for ADS and MWO

RoHS
COMPLIANT



Absolute Maximum Ratings (not simultaneous) at 25 °C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DS}	120	Volts	25 °C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25 °C
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Forward Gate Current	I_{GMAX}	30	mA	25 °C
Maximum Drain Current ¹	I_{DMAX}	12	A	25 °C
Thermal Resistance, Junction to Case (packaged) ²	$R_{\theta JC}$	1.39	°C/W	
Thermal Resistance, Junction to Case (die only)	$R_{\theta JC}$	0.8	°C/W	85 °C
Mounting Temperature (30 seconds)	T_S	320	°C	30 seconds

Notes:

¹ Current limit for long term, reliable operation

² Eutectic die attach using 80/20 AuSn mounted to a 60 mil thick CuMoCu carrier

Electrical Characteristics (Frequency = 4 GHz unless otherwise stated; $T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	$V_{DS} = 10\text{ V}, I_D = 28.8\text{ mA}$
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	V_{DC}	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}$
Drain Current	I_{DSS}	23.2	28.0	-	A	$V_{DS} = 6.0\text{ V}, V_{GS} = 2.0\text{ V}$
Drain-Source Breakdown Voltage	V_{BD}	84	-	-	V	$V_{GS} = -8\text{ V}, I_D = 28.8\text{ mA}$
On Resistance	R_{ON}	-	0.08	-	Ω	$V_{DS} = 0.10\text{ V}$
Gate Forward Voltage	V_{G-ON}	-	1.9	-	V	$I_{GS} = 28.8\text{ mA}$
RF Characteristics						
Small Signal Gain	G_{SS}	-	15	-	dB	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}$
Saturated Output Power ¹	P_{SAT}	-	120	-	W	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}$
Drain Efficiency ²	η	-	65	-	%	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}, P_{SAT} = 120\text{ W}$
Intermodulation Distortion	IM3	-	-30	-	dBc	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}, P_{OUT} = 120\text{ W PEP}$
Output Mismatch Stress ³	VSWR	-	-	10 : 1	Ψ	$V_{DD} = 28\text{ V}, I_{DQ} = 1000\text{ mA}, P_{OUT} = 120\text{ W (CW)}$
Dynamic Characteristics						
Input Capacitance	C_{GS}	-	31.2	-	pF	$V_{DS} = 28\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$
Output Capacitance	C_{DS}	-	10.6	-	pF	$V_{DS} = 28\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$
Feedback Capacitance	C_{GD}	-	1.5	-	pF	$V_{DS} = 28\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$

Notes:

¹ P_{SAT} is defined as $I_G = 2.8\text{ mA}$

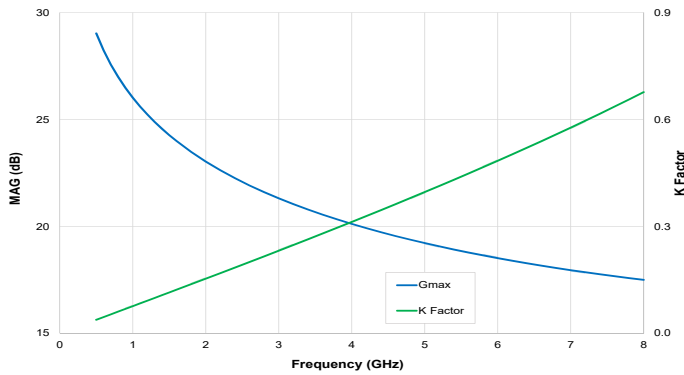
² Drain Efficiency = P_{OUT} / P_{DC}

³ No damage at all phase angles

Typical Performance

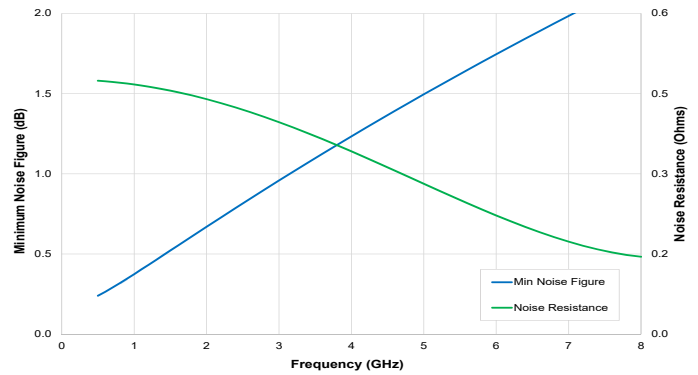
Simulated Maximum Available Gain and K Factor

$$V_{DD} = 28 \text{ V}, I_{DQ} = 1000 \text{ mA}$$



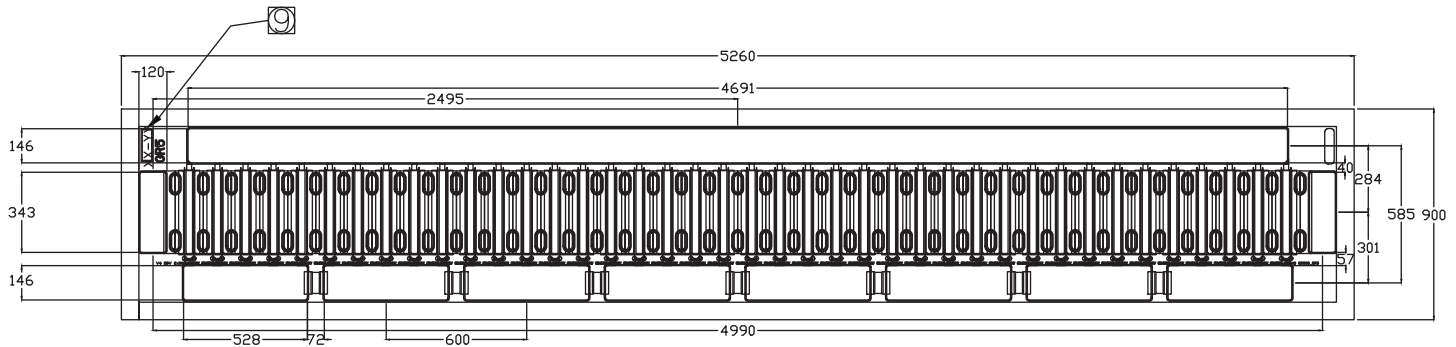
Simulated Minimum Noise Figure and Noise Resistance vs. Frequency

$$V_{DD} = 28 \text{ V}, I_{DQ} = 1000 \text{ mA}$$



Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Die Dimensions (units in microns)



Assembly Notes:

- Recommended solder is AuSn (80/20) solder. Refer to Cree's website for the Eutectic Die Bond Procedure application note at <https://www.wolfspeed.com/rf/document-library>
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.
- Use the die label (XX-YY) for correct orientation.



Typical Package S-Parameters for CG2H80120D
(Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 500\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
0.5	0.958	-174.57	5.11	84.00	0.009	-5.31	0.829	-176.75
0.6	0.958	-175.39	4.24	81.90	0.009	-7.28	0.831	-176.74
0.7	0.958	-175.96	3.62	79.93	0.009	-9.11	0.833	-176.65
0.8	0.959	-176.38	3.15	78.05	0.009	-10.85	0.835	-176.53
0.9	0.959	-176.71	2.78	76.24	0.009	-12.52	0.837	-176.39
1.0	0.960	-176.96	2.49	74.49	0.009	-14.14	0.839	-176.23
1.1	0.960	-177.16	2.25	72.79	0.009	-15.70	0.842	-176.08
1.2	0.961	-177.32	2.04	71.12	0.009	-17.23	0.845	-175.92
1.3	0.962	-177.46	1.87	69.50	0.008	-18.72	0.848	-175.77
1.4	0.962	-177.58	1.72	67.91	0.008	-20.17	0.851	-175.63
1.5	0.963	-177.68	1.59	66.36	0.008	-21.58	0.854	-175.49
1.6	0.964	-177.76	1.48	64.84	0.008	-22.96	0.857	-175.37
1.8	0.965	-177.91	1.29	61.91	0.008	-25.61	0.863	-175.15
2.0	0.966	-178.03	1.13	59.11	0.008	-28.14	0.870	-174.98
2.2	0.968	-178.14	1.00	56.45	0.008	-30.53	0.876	-174.85
2.4	0.969	-178.23	0.90	53.90	0.007	-32.80	0.883	-174.75
2.6	0.971	-178.32	0.81	51.48	0.007	-34.94	0.889	-174.69
2.8	0.972	-178.40	0.73	49.18	0.007	-36.97	0.895	-174.67
3.0	0.973	-178.48	0.67	46.99	0.007	-38.88	0.901	-174.66
3.2	0.975	-178.56	0.61	44.90	0.007	-40.69	0.906	-174.69
3.4	0.976	-178.64	0.56	42.92	0.007	-42.39	0.911	-174.73
3.6	0.977	-178.72	0.51	41.04	0.006	-44.00	0.916	-174.78
3.8	0.978	-178.79	0.47	39.25	0.006	-45.51	0.921	-174.85
4.0	0.979	-178.86	0.44	37.54	0.006	-46.94	0.925	-174.94
4.2	0.980	-178.94	0.41	35.92	0.006	-48.29	0.929	-175.02
4.4	0.981	-179.01	0.38	34.37	0.006	-49.56	0.933	-175.12
4.6	0.982	-179.08	0.35	32.89	0.005	-50.76	0.936	-175.22
4.8	0.982	-179.15	0.33	31.48	0.005	-51.89	0.940	-175.32
5.0	0.983	-179.22	0.31	30.13	0.005	-52.95	0.943	-175.43
5.2	0.984	-179.29	0.29	28.84	0.005	-53.96	0.946	-175.54
5.4	0.984	-179.36	0.27	27.61	0.005	-54.92	0.948	-175.65
5.6	0.985	-179.43	0.26	26.43	0.005	-55.82	0.951	-175.76
5.8	0.985	-179.50	0.24	25.29	0.005	-56.67	0.953	-175.87
6.0	0.986	-179.56	0.23	24.20	0.005	-57.48	0.955	-175.97
6.2	0.986	-179.63	0.22	23.15	0.004	-58.24	0.957	-176.08
6.4	0.987	-179.69	0.21	22.14	0.004	-58.97	0.959	-176.19
6.6	0.987	-179.76	0.19	21.17	0.004	-59.65	0.961	-176.29
6.8	0.988	-179.82	0.19	20.24	0.004	-60.30	0.963	-176.4
7.0	0.988	-179.88	0.18	19.33	0.004	-60.92	0.964	-176.50
7.2	0.988	-179.94	0.17	18.46	0.004	-61.50	0.966	-176.60
7.4	0.989	-179.99	0.16	17.62	0.004	-62.06	0.967	-176.70
7.6	0.989	-179.93	0.15	16.80	0.004	-62.59	0.968	-176.79
7.8	0.989	-179.87	0.15	16.01	0.004	-63.09	0.969	-176.89
8.0	0.990	-179.82	0.14	15.24	0.004	-63.56	0.971	-176.98

To download the s-parameters in s2p format, go to the [CG2H80120D](#) product page and click on the documentation tab.



Typical Package S-Parameters for CG2H80120D
(Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 1000\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
0.5	0.969	-175.19	5.14	85.64	0.006	-3.62	0.864	-177.97
0.6	0.969	-175.95	4.28	83.93	0.006	-5.18	0.865	-177.99
0.7	0.969	-176.50	3.66	82.33	0.006	-6.63	0.866	-177.96
0.8	0.969	-176.90	3.19	80.82	0.006	-8.00	0.867	-177.90
0.9	0.969	-177.22	2.83	79.35	0.006	-9.31	0.868	-177.82
1.0	0.970	-177.46	2.53	77.93	0.006	-10.59	0.869	-177.73
1.1	0.970	-177.67	2.29	76.55	0.006	-11.83	0.871	-177.63
1.2	0.970	-177.83	2.09	75.19	0.006	-13.04	0.872	-177.53
1.3	0.970	-177.97	1.92	73.86	0.006	-14.22	0.873	-177.43
1.4	0.971	-178.09	1.77	72.55	0.006	-15.38	0.875	-177.33
1.5	0.971	-178.19	1.65	71.26	0.006	-16.52	0.877	-177.23
1.6	0.971	-178.28	1.53	69.99	0.006	-17.64	0.878	-177.13
1.8	0.972	-178.43	1.35	67.52	0.006	-19.81	0.882	-176.95
2.0	0.973	-178.55	1.19	65.13	0.006	-21.91	0.885	-176.79
2.2	0.973	-178.66	1.07	62.81	0.006	-23.93	0.889	-176.64
2.4	0.974	-178.74	0.96	60.57	0.006	-25.87	0.893	-176.52
2.6	0.975	-178.82	0.87	58.40	0.006	-27.74	0.897	-176.42
2.8	0.976	-178.90	0.80	56.31	0.006	-29.53	0.901	-176.33
3.0	0.977	-178.96	0.73	54.29	0.005	-31.25	0.904	-176.27
3.2	0.977	-179.03	0.67	52.34	0.005	-32.90	0.908	-176.22
3.4	0.978	-179.09	0.62	50.46	0.005	-34.48	0.912	-176.19
3.6	0.979	-179.15	0.58	48.65	0.005	-35.99	0.915	-176.17
3.8	0.979	-179.21	0.54	46.91	0.005	-37.43	0.919	-176.17
4.0	0.980	-179.27	0.50	45.23	0.005	-38.80	0.922	-176.17
4.2	0.981	-179.33	0.47	43.61	0.005	-40.11	0.925	-176.19
4.4	0.981	-179.38	0.44	42.06	0.005	-41.37	0.929	-176.22
4.6	0.982	-179.44	0.41	40.56	0.005	-42.56	0.931	-176.25
4.8	0.983	-179.50	0.38	39.11	0.004	-43.70	0.934	-176.29
5.0	0.983	-179.55	0.36	37.72	0.004	-44.79	0.937	-176.34
5.2	0.984	-179.61	0.34	36.37	0.004	-45.82	0.940	-176.39
5.4	0.984	-179.67	0.32	35.08	0.004	-46.81	0.942	-176.44
5.6	0.985	-179.72	0.30	33.83	0.004	-47.75	0.944	-176.50
5.8	0.985	-179.78	0.29	32.62	0.004	-48.64	0.947	-176.57
6.0	0.986	-179.83	0.27	31.45	0.004	-49.49	0.949	-176.63
6.2	0.986	-179.89	0.26	30.33	0.004	-50.30	0.951	-176.70
6.4	0.986	-179.94	0.25	29.24	0.004	-51.08	0.952	-176.76
6.6	0.987	-180.00	0.24	28.19	0.004	-51.81	0.954	-176.83
6.8	0.987	179.95	0.23	27.17	0.004	-52.51	0.956	-176.90
7.0	0.987	179.9	0.22	26.18	0.003	-53.18	0.958	-176.97
7.2	0.988	179.84	0.21	25.22	0.003	-53.81	0.959	-177.05
7.4	0.988	179.79	0.20	24.29	0.003	-54.42	0.961	-177.12
7.6	0.988	179.73	0.19	23.39	0.003	-54.99	0.962	-177.19
7.8	0.989	179.68	0.18	22.52	0.003	-55.54	0.963	-177.26
8.0	0.989	179.63	0.17	21.67	0.003	-56.05	0.964	-177.33

To download the s-parameters in s2p format, go to the [CG2H80120D](#) product page and click on the documentation tab.



Product Ordering Information

Order Number	Description	Unit of Measure	Image
CG2H80120D	GaN HEMT Bare Die	Each	



For more information, please contact:

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Sales Contact
rfsales@cree.com

Notes & Disclaimer

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